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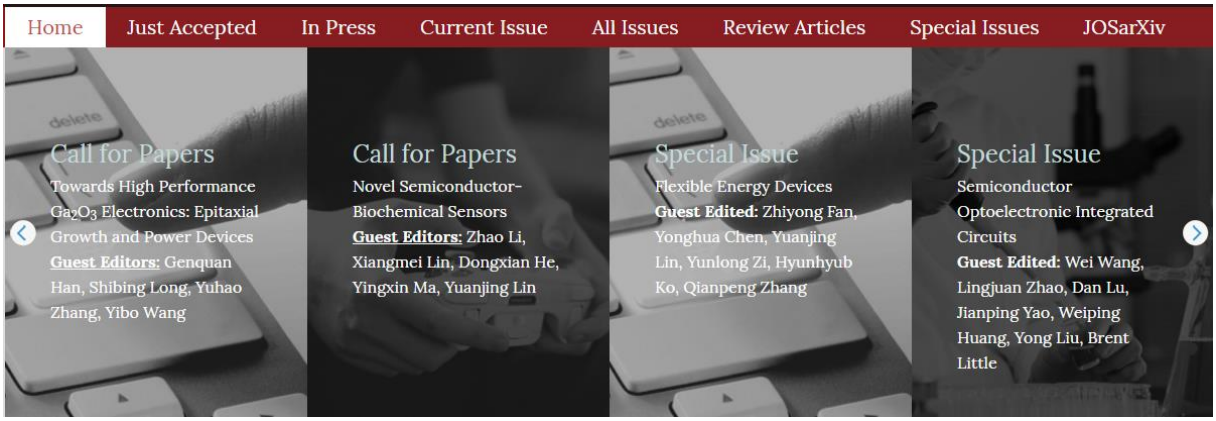

A Special Issue on

"Towards High Performance Ga_2O_3 Electronics: Epitaxial Growth and Power Devices"

CALL FOR PAPERS

Gallium oxide (Ga_2O_3) is graining tremendous traction for power electronics applications due to its high breakdown field. Ga_2O_3 possesses an ultra-wide bandgap of 4.8 eV, well above SiC and GaN (3.3~3.4 eV). Extensive research efforts have been devoted to developing effective epitaxial growth method for high quality Ga_2O_3 films and exploring high performance Ga_2O_3 electronic devices. Exciting research achievements have been achieved in Ga_2O_3 large size substrate, epitaxial growth techniques, and devices. These progresses make Ga_2O_3 promising for realizing more efficient, high power, high frequency power electronics.

This special issue focuses on recent progress in the topics related to Ga_2O_3 epitaxial growth and electronic devices. Both experimental and theoretical works will be accepted. We invite submission of original research articles/communications and comprehensive review papers to this special issue. The topics to be covered in this special issue include, but are not limited to:

- High voltage Ga_2O_3 electronic devices;
- Ga_2O_3 radio frequency devices;
- Ga_2O_3 heterojunction devices;
- High quality epitaxial growth of Ga_2O_3 films;
- Heterogeneous integration of Ga_2O_3 on foreign substrates;
- Theoretical modelling and simulation of Ga_2O_3 device;
- Large-size Ga_2O_3 single crystals and wafers.

GUEST EDITORS

Prof. Genquan Han, School of Microelectronics, Xidian University, Xian'an, Shaanxi 710071, China.
E-mail: gqhan@xidian.edu.cn

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Prof. Shibing Long, School of Microelectronics, University of Science and Technology of China, Hefei, Anhui 230026, China.
E-mail: shibinglong@ustc.edu.cn

Assist. Prof. Yuhao Zhang, Center for Power Electronics Systems (CPES), Virginia Polytechnic Institute and State University, Blacksburg, VA 24060 USA.
E-mail: yhzhang@vt.edu

Dr. Yibo Wang, Platform for Characterization & Test, Suzhou Institute of Nano-Tech and Nano-Bionics (SINANO), Chinese Academy of Sciences, Suzhou 215123, China.
E-mail: ybwang2022@sinano.ac.cn

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